Schottky Barrier Rectifier, Trench-based

NRTS860PFS, NRVTS860PFS

This TO-277 trench Schottky rectifier provides fast switching performance in a compact thermally efficient package. The TO-277 package provides an excellent alternative to the DPAK, offering thermal performance nearly as good in a package occupying less than half the board space. Its low profile makes it a good option for flat panel display and other applications with limited vertical clearance. The device offers low leakage over temperature making it a good match for applications requiring low quiescent current.

Features

- Package Provides Capability of Inspection and Probe After Board Mounting
- Low Forward Voltage Drop
- 175°C Operating Junction Temperature
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94–0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements

Applications

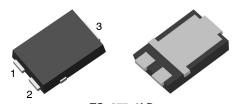
- Excellent Alternative to DPAK in Space-Constrained Automotive Applications
- Low Leakage for Higher Temperature Operation
- Output Rectification in Compact Portable Consumer Applications
- Freewheeling Diode used with Inductive Loads



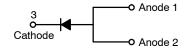
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SCHOTTKY BARRIER RECTIFIER, 8 AMPERES 60 VOLTS



TO-277-3LD CASE 340CZ



MARKING DIAGRAM

TS860 AWLYW

TS860 = Specific Device Code A = Assembly Location

Y = Year

W = Work Week WL = Wafer Lot

ORDERING INFORMATION

Device	Package	Shipping†
NRTS860PFST3G	TO-277 (Pb-Free)	1500 / Tape & Reel
NRVTS860PFST3G	TO-277 (Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NRTS860PFS, NRVTS860PFS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	60	V
Average Rectified Forward Current $(T_C = 165^{\circ}C)$	I _{F(AV)}	8	А
Peak Repetitive Forward Current, (T _C = 163°C, Square Wave, Duty = 0.5)	I _{FRM}	16	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	150	А
Storage Temperature Range	T _{stg}	-65 to +175	°C
Operating Junction Temperature	TJ	-55 to +175	°C
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		M4	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Assumes 600 mm², 1 oz. copper bond pad on a FR4 board)	$R_{ hetaJA}$	69	°C/W
Thermal Resistance, Junction-to-Case, Top (Assumes 600 mm², 1 oz. copper bond pad on a FR4 board)	$R_{\theta JCT}$	62	°C/W
Thermal Resistance, Junction-to-Case, Bottom (Assumes 600 mm², 1 oz. copper bond pad on a FR4 board)	$R_{\theta JCB}$	2.2	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Тур	Max	Unit
Instantaneous Forward Voltage (Note 1) $ \begin{aligned} (I_F = 4 \ A, \ T_J = 25^{\circ}\text{C}) \\ (I_F = 4 \ A, \ T_J = 125^{\circ}\text{C}) \\ (I_F = 8 \ A, \ T_J = 25^{\circ}\text{C}) \\ (I_F = 8 \ A, \ T_J = 125^{\circ}\text{C}) \end{aligned} $	V _F	0.49 0.41 0.56 0.51	- - 0.64 0.61	V
Instantaneous Reverse Current (Note 1) (V _R = Rated dc Voltage, T _J = 25°C) (V _R = Rated dc Voltage, T _J = 125°C)	I _R	4.0 3.0	70 30	μA mA
Junction Capacitance $(V_R = 1 \text{ V, } T_J = 25^{\circ}\text{C, 1 MHz})$	СЈ	870	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

NRTS860PFS, NRVTS860PFS

TYPICAL CHARACTERISTICS

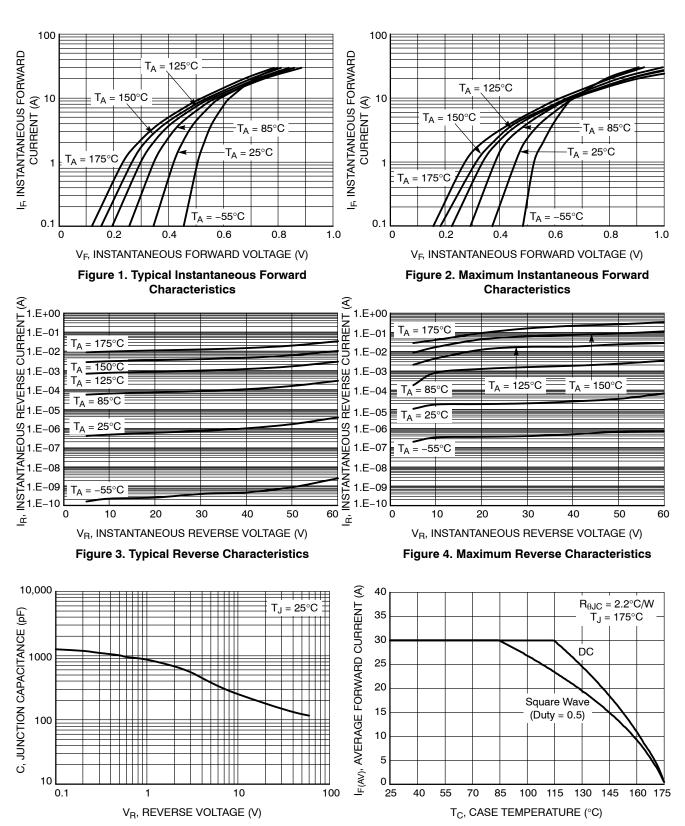


Figure 5. Typical Junction Capacitance

NRTS860PFS, NRVTS860PFS

TYPICAL CHARACTERISTICS

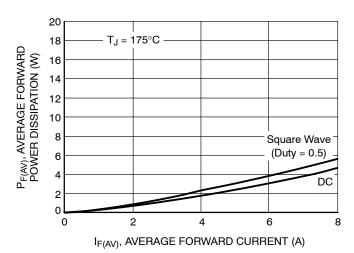


Figure 7. Forward Power Dissipation

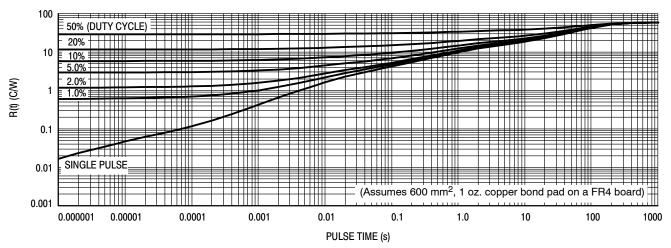


Figure 8. Typical Thermal Characteristics, Junction to Ambient

D1

Κ

THP VIFW

В

E1

Ε

TO-277-3LD CASE 340CZ **ISSUE A**

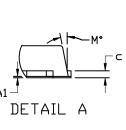
NOTES:

DATE 14 FEB 2020



- 2. CONTROLLING DIMENSION: MILLIMETERS DIMENSIONS b, b1,b2,b3,b6 AND c TO BE MEASURED ON FLAT SECTION OF THE LEAD, BETWEEN 0.13 AND 0.25mm FROM LEAD TIP.
- COPLANARITY APPLES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
- 5. POSITIONAL TOLERANCE APPLIES TO THE TERMINALS AND EXPOSED PAD.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
- 7. DIMENSIONS D AND E TO BE DETERMINED AT DATUM PLANE C.

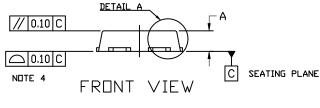
MILLIMETERS



	DIM	MIN.	N□M.	MAX.
~ M°	Α	1.00	1.10	1.20
	A1		0.01	0.05
	b	1.13	1.18	1.28
	b1	b1 0.70 REF		
ļ	b2	1.98	2.03	2.13
AIL A	b3		1.20 REF	
	b4		0.71 REF	
	С		0.20 REF	
	D	4.45	4.60	4.75
	D1	4.35	4.40	4.45

D2

	MILLIMETERS		
DIM	MIN.	N□M.	MAX.
E	6.35	6.50	6.65
E1	6.05	6.10	6.15
E2	4.50	4.60	4.70
E3	3.84	3.94	4.04
E4	0.98 REF		
e	2.13 BSC		
K	0.85 REF		
K1	0.40 REF		
L	0.90	1.05	1.20
L1	0.02		
М			12*

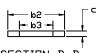


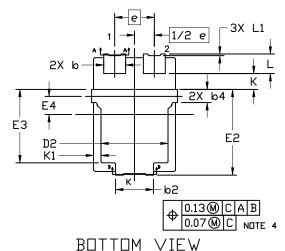


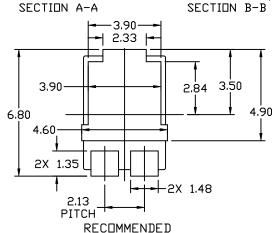
3.50

3.60

3.70







MOUNTING FOOTPRINT For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ", may or may not be present. Some products may not follow the Generic Marking.

GENERIC MARKING DIAGRAM*

XXXXXX = Specific Device Code

XXXXXX **AWLYW**

98AON97727G

= Assembly Location Υ = Year

W = Work Week WL = Wafer Lot

DOCUMENT NUMBER:

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